20V P-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI5060-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_C = +25°C
-20V	2.5mΩ @ V_{GS} = -10V	-60A
	3.5mΩ @ V_{GS} = -4.5V	-60A

Description

This new generation P-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$ yet maintain superior switching performance.

Applications

- Load Switch
- Notebook Battery Power Management

Features

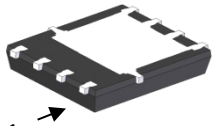
- Thermally Efficient Package – Cooler Running Applications
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On State Losses
- <1.1mm Package Profile – Ideal for Thin Applications
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Mechanical Data

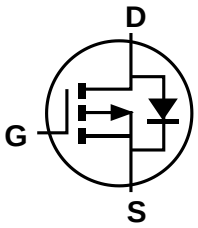
- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.097 grams (Approximate)

PowerDI5060-8 (Type K)

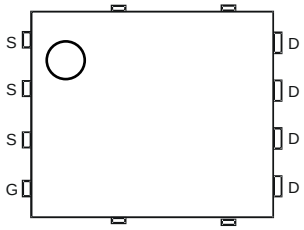
Top View



Bottom View



Internal Schematic



Top View
Pin Configuration

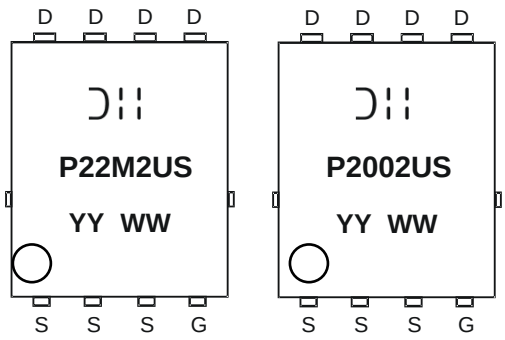
Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP22M2UPS-13	PowerDI5060-8 (Type K)	2,500	Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI5060-8 (Type K)



= Manufacturer's Marking
P22M2US or P2002US = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 21 = 2021)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current, V_{GS} = 10V (Note 5)	Steady State (Note 6)	T_C = +25°C T_C = +70°C	I_D	-60 -60	A
		T_A = +25°C T_A = +70°C		-42 -33.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-100	A
Continuous Body Diode Forward Current (Note 5)	Steady State (Note 6)	T_C = +25°C	I_S	-60	A
		T_A = +25°C		-5.6	A
Avalanche Current, L = 0.1mH			I_{AS}	-37	A
Avalanche Energy, L = 0.1mH			E_{AS}	69.8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P_D	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	55	°C/W
Total Power Dissipation (Note 6)	Steady State	P_D	104	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	0.9	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Note: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
6. Package limited.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-10	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±12V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	—	-1.4	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	2.5	mΩ	V_{GS} = -10V, I_D = -25A
		—	—	3.5		V_{GS} = -4.5V, I_D = -20A
		—	—	5.0		V_{GS} = -2.5V, I_D = -15A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	12826	—	pF	V_{DS} = -10V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	2547	—		
Reverse Transfer Capacitance	C_{rss}	—	1924	—		
Gate Resistance	R_G	—	4.2	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -10V)	Q_g	—	476	—	nC	V_{DS} = -10V, I_D = -20A
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	228	—		
Gate-Source Charge	Q_{gs}	—	24.8	—		
Gate-Drain Charge	Q_{gd}	—	61.9	—		
Turn-On Delay Time	$t_{D(ON)}$	—	14.2	—	ns	V_{DD} = -10V, V_{GEN} = -4.5V, R_{GEN} = 1Ω, I_D = -10A
Turn-On Rise Time	t_R	—	35.4	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	361	—		
Turn-Off Fall Time	t_F	—	224	—		
BODY DIODE CHARACTERISTICS						
Diode Forward Voltage	V_{SD}	—	-0.58	—	V	V_{GS} = 0V, I_S = -5A
Reverse Recovery Time (Note 8)	t_{RR}	—	137	—	ns	I_F = -10A, di/dt = 100A/µs
Reverse Recovery Charge (Note 8)	Q_{rr}	—	221	—	nC	
Reverse Recovery Fall Time (Note 8)	t_a	—	39	—	ns	
Reverse Recovery Rise Time (Note 8)	t_b	—	98	—		

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

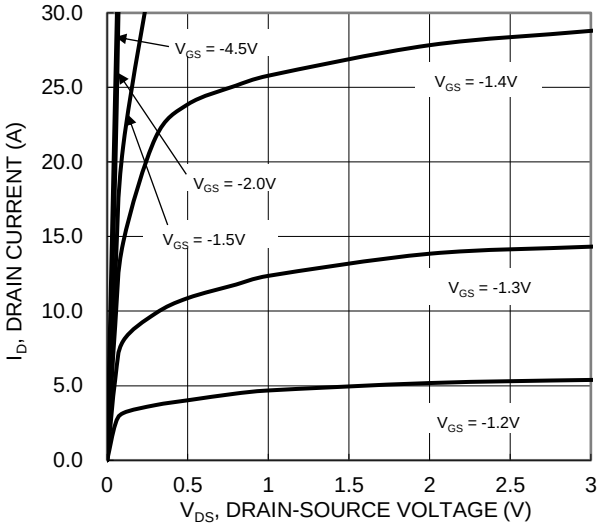


Figure 1. Typical Output Characteristic

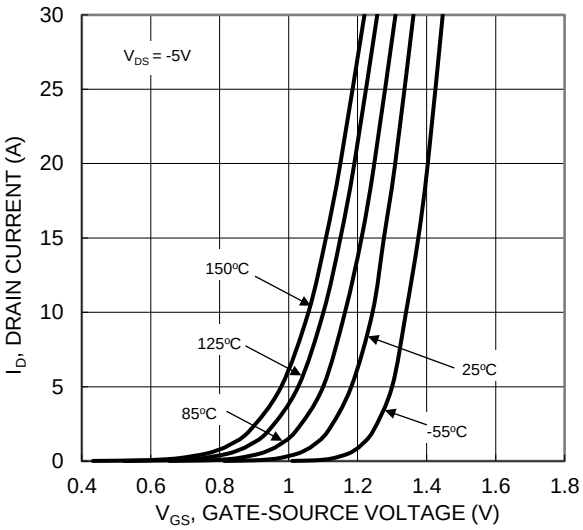


Figure 2. Typical Transfer Characteristic

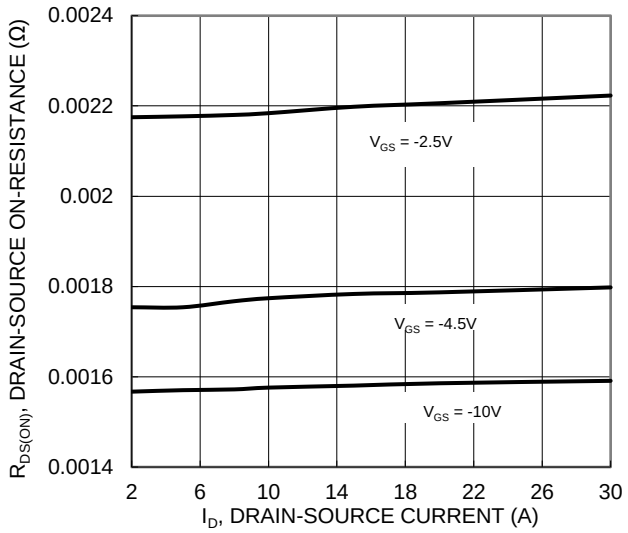


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

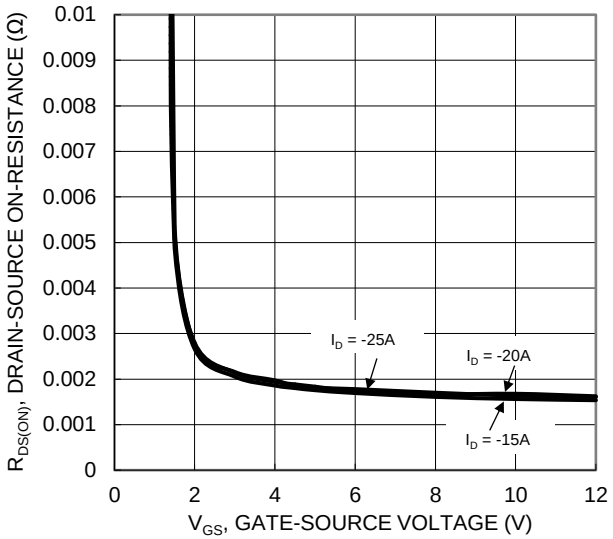


Figure 4. Typical Transfer Characteristic

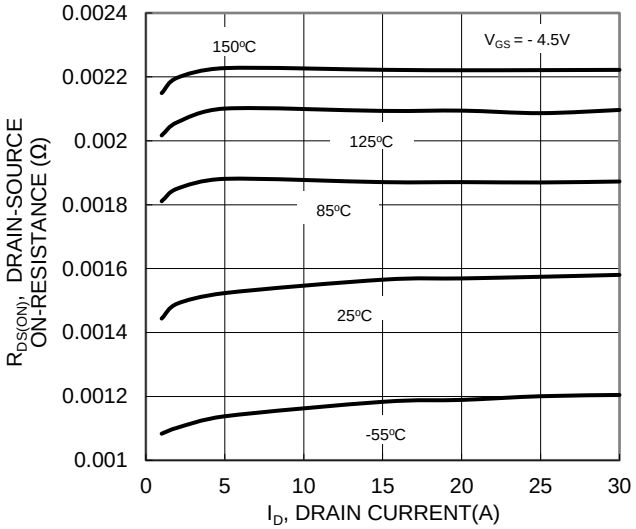


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

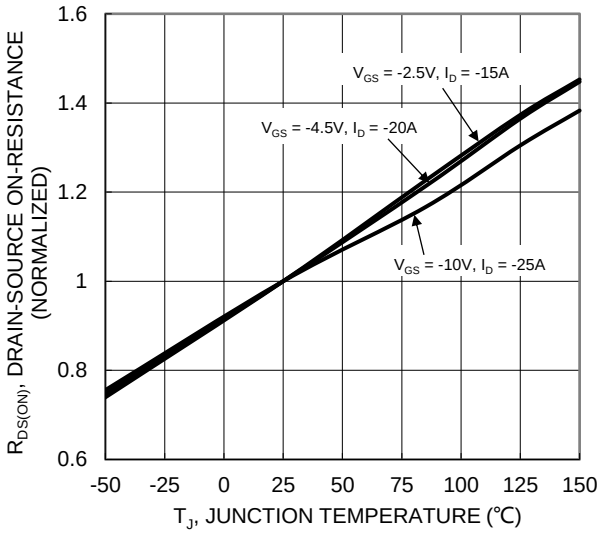


Figure 6. On-Resistance Variation with Temperature

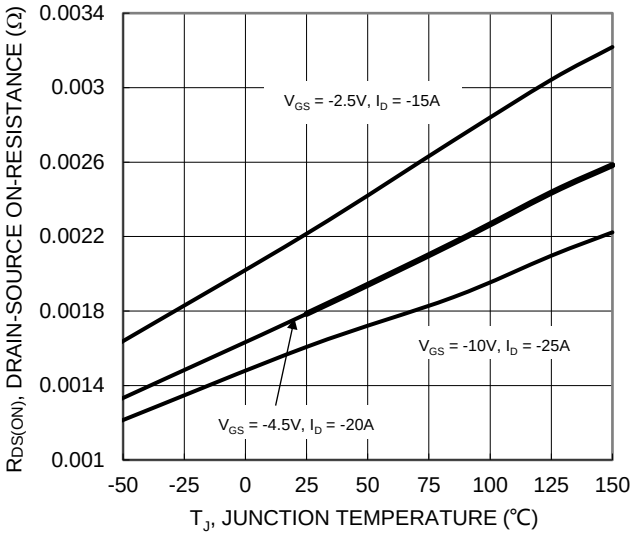


Figure 7. On-Resistance Variation with Temperature

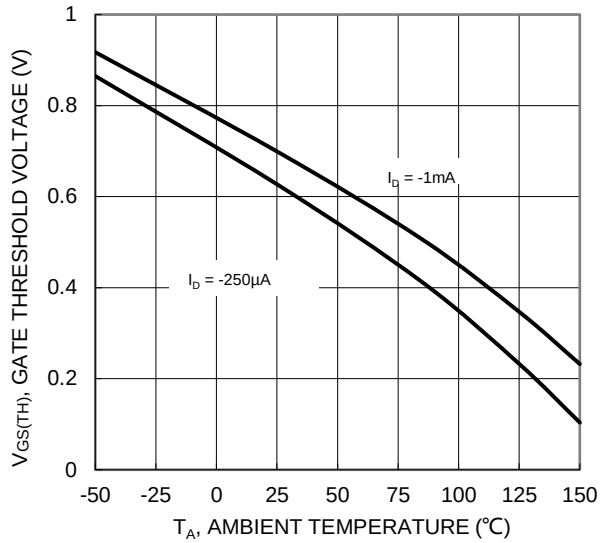


Figure 8. Gate Threshold Variation vs. Ambient Temperature

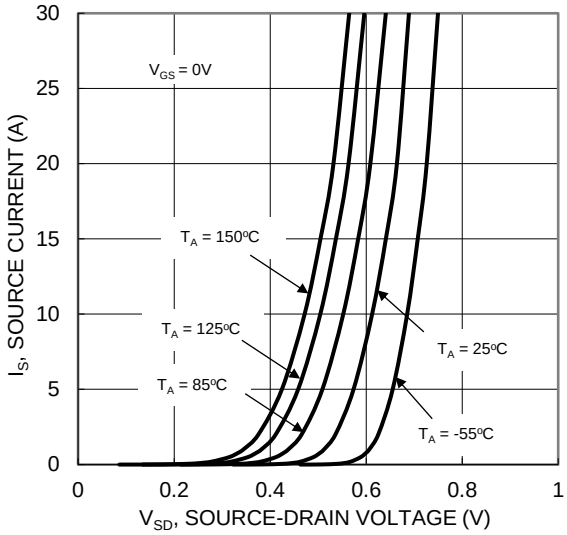


Figure 9. Diode Forward Voltage vs. Current

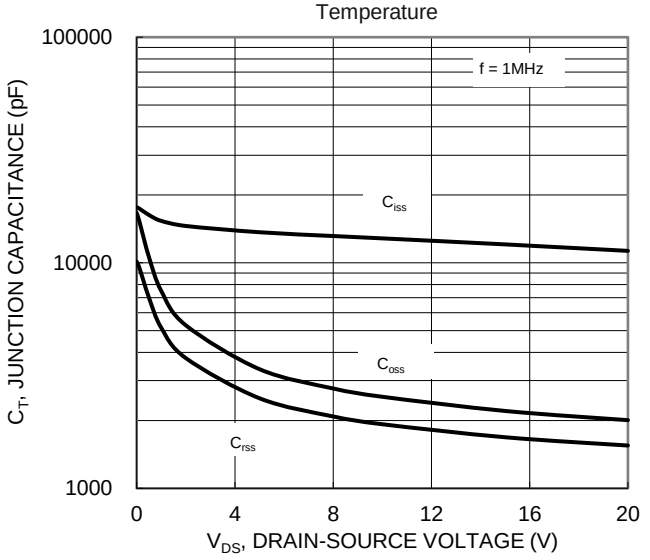


Figure 10. Typical Junction Capacitance

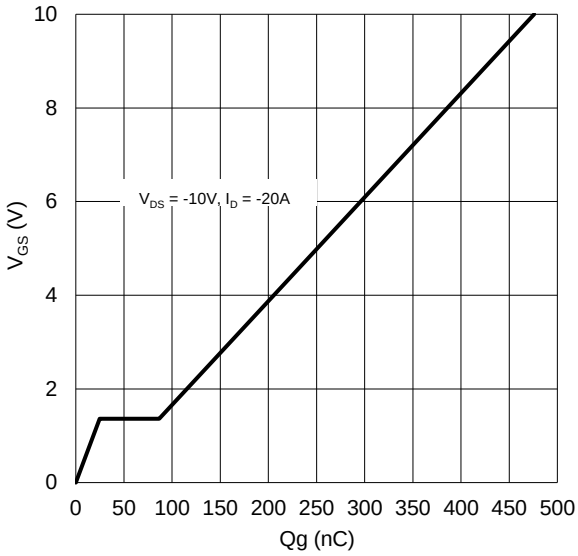


Figure 11. Gate Charge

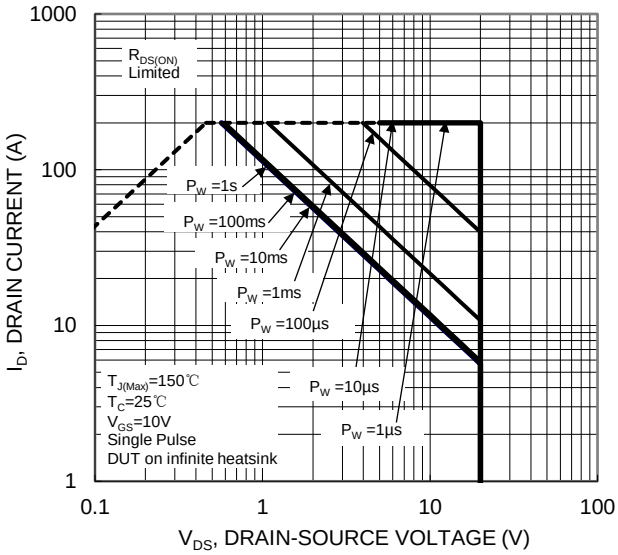


Figure 12. SOA, Safe Operation Area

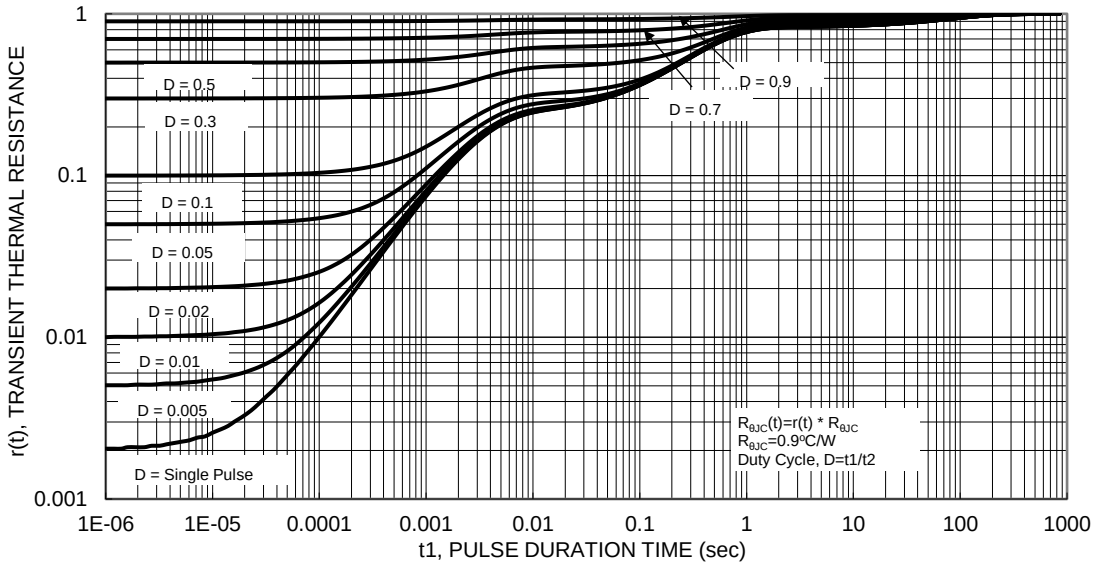
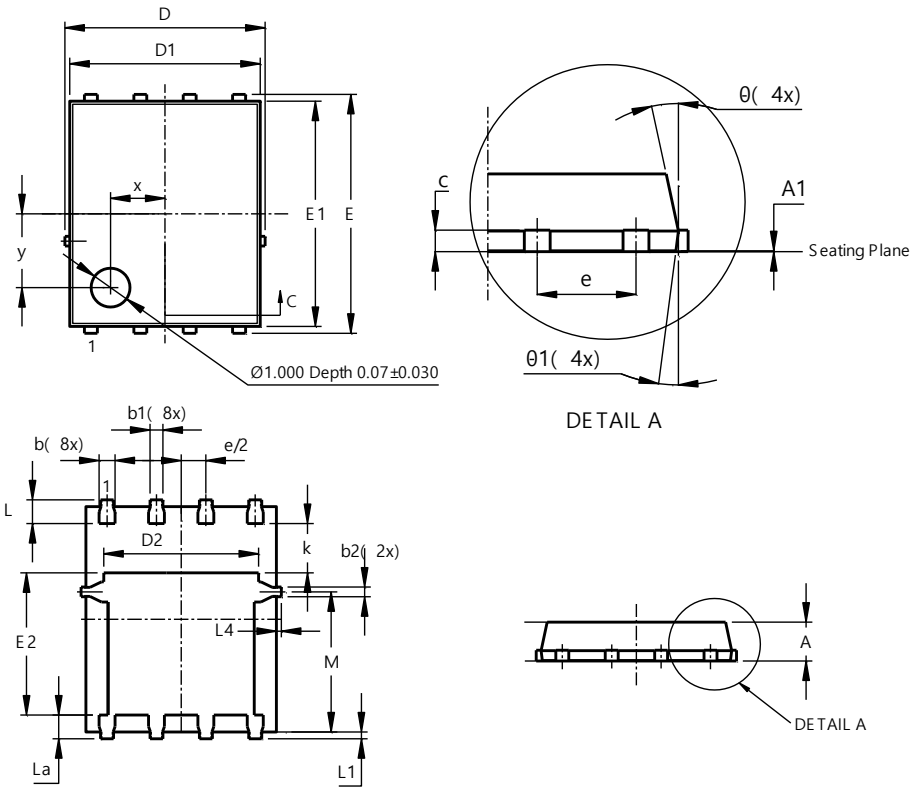


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)

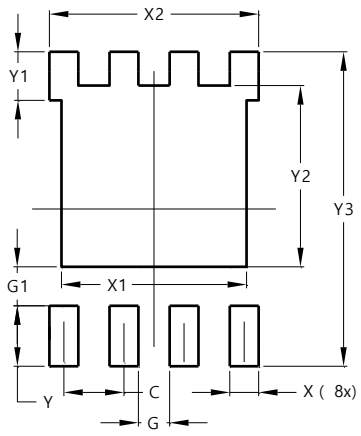


PowerDI5060-8 (Type K)			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.725	3.66
e	1.27BSC		
k	-	-	1.27
L	0.51	0.71	0.61
La	0.51	0.675	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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